



## Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
30	0.022 at V <sub>GS</sub> = 10 V	8	7
	0.027 at V <sub>GS</sub> = 4.5 V	7.9	

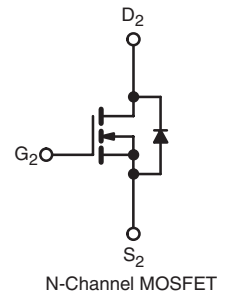
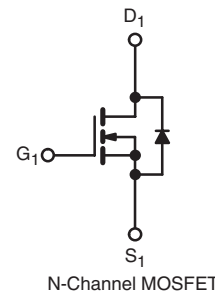
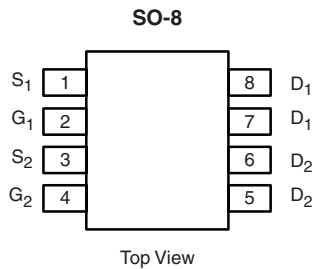
## FEATURES

- Halogen-free
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested

RoHS  
COMPLIANT

## APPLICATIONS

- DC/DC
- Notebook System Power



Ordering Information: Si4804CDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	8.0	A	
	T <sub>C</sub> = 70 °C	7.1		
	T <sub>A</sub> = 25 °C	7.1 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	5.5 <sup>b, c</sup>		
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	30	A	
Source-Drain Current Diode Current	T <sub>C</sub> = 25 °C	2.4		
	T <sub>A</sub> = 25 °C	1.8 <sup>b, c</sup>		
Pulsed Source-Drain Current	I <sub>SM</sub>	30	mJ	
Single Pulse Avalanche Current	L = 0.1 mH I <sub>AS</sub>	10		
Single Pulse Avalanche Energy	E <sub>AS</sub>	5	W	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	3.1		
	T <sub>C</sub> = 70 °C	2		
	T <sub>A</sub> = 25 °C	2 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	1.28 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	49	62.5	°C/W
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	32	40	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 120 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		31		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.1		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.2		2.4	V
Gate Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}$		0.018	0.022	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 6.5\text{ A}$		0.022	0.027	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 7.5\text{ A}$		20		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		865		$\mu\text{F}$
Output Capacitance	$C_{oss}$			131		
Reverse Transfer Capacitance	$C_{rss}$			66		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}$		15.4	23	nC
		N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 7.5\text{ A}$		7	10.5	
Gate-Source Charge	$Q_{gs}$			2.3		
Gate-Drain Charge	$Q_{gd}$		2.2			
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.4	1.9	3.8	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		9	18	ns
Rise Time	$t_r$			12	24	
Turn-Off Delay Time	$t_{d(off)}$			17	34	
Fall Time	$t_f$			9	18	
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		17	34	
Rise Time	$t_r$			13	26	
Turn-Off Delay Time	$t_{d(off)}$			19	35	
Fall Time	$t_f$			9	18	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			2.4	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				30	
Body Diode Voltage	$V_{SD}$	$I_S = 1.8\text{ A}$		0.77	1.1	V
Body Diode Reverse Recovery Time	$t_{rr}$	N-Channel $I_F = 5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		16	32	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			8	16	nC
Reverse Recovery Fall Time	$t_a$			10		ns
Reverse Recovery Rise Time	$t_b$			6		

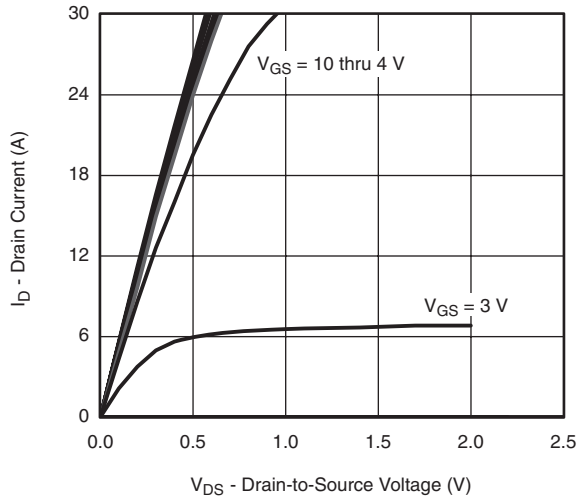
## Notes:

- a. Guaranteed by design, not subject to production testing.  
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$

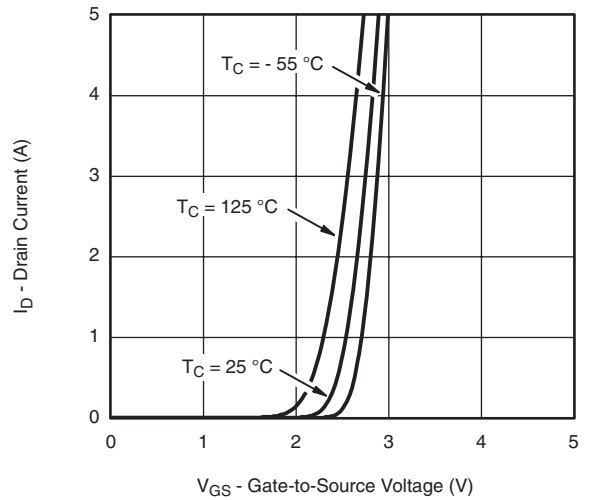
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



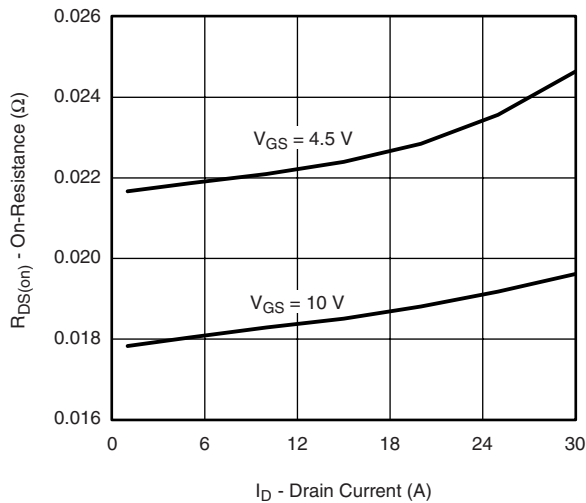
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



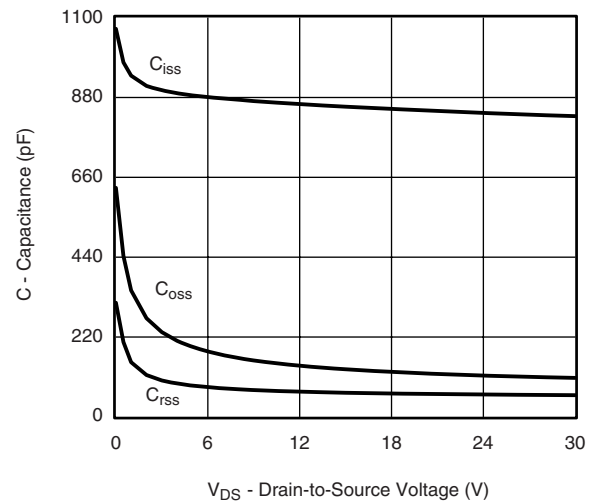
**Output Characteristics**



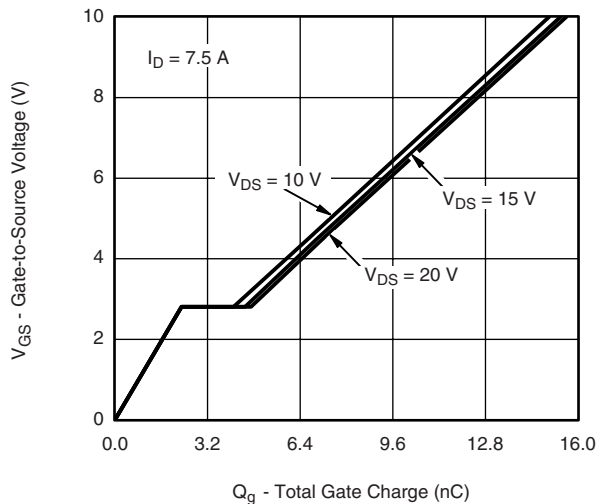
**Transfer Characteristics**



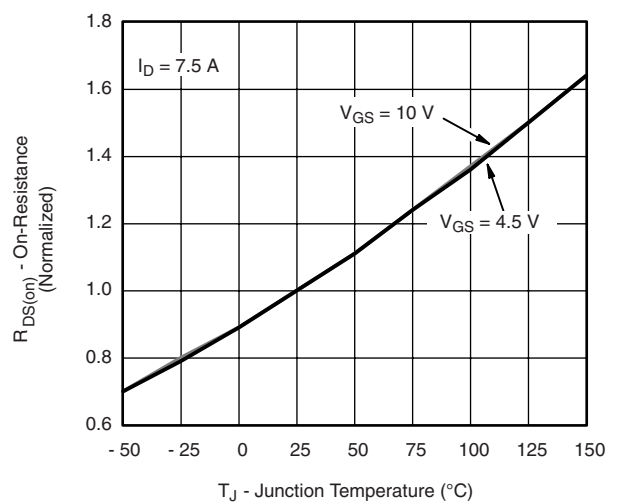
**On-Resistance vs. Drain Current**



**Capacitance**



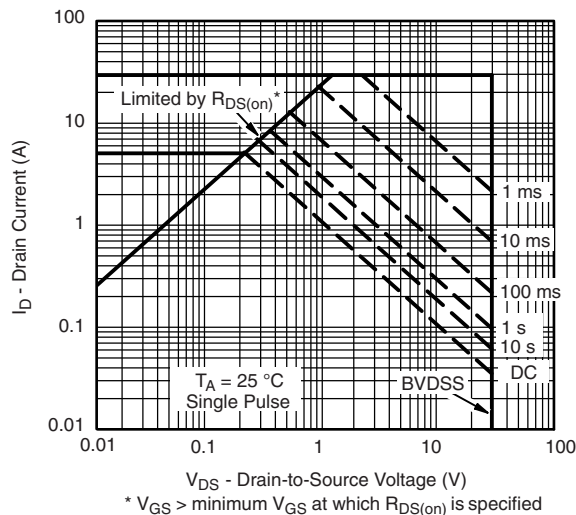
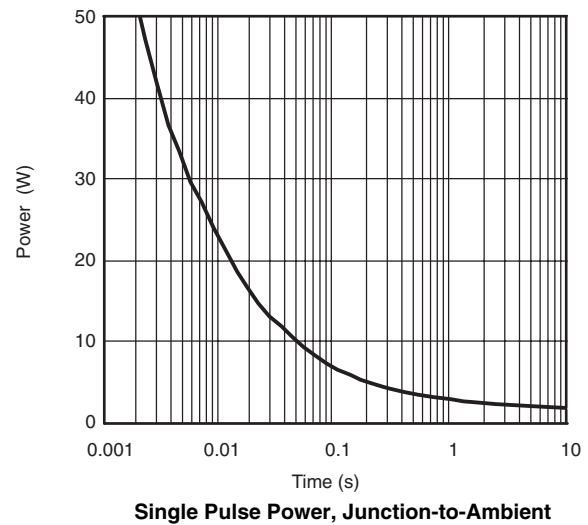
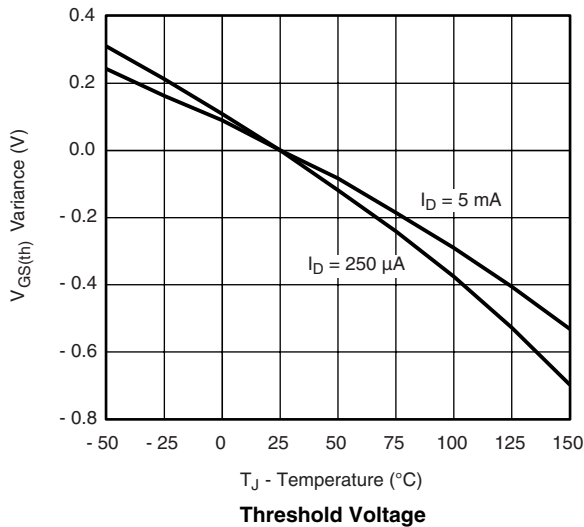
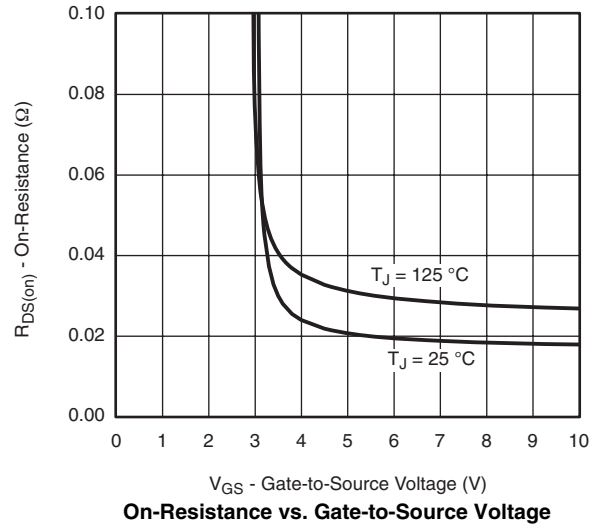
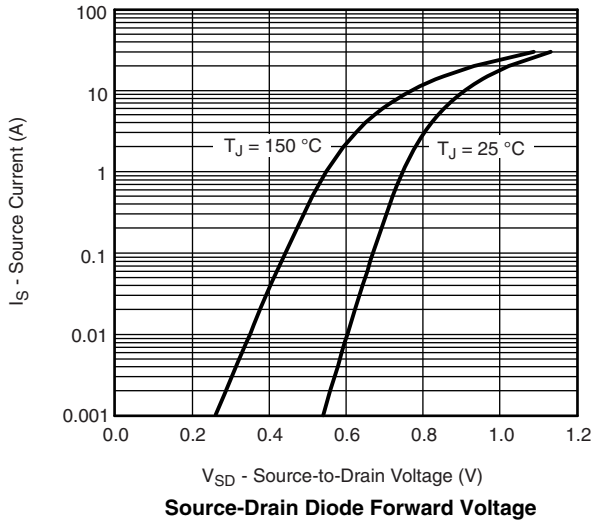
**Gate Charge**



**On-Resistance vs. Junction Temperature**

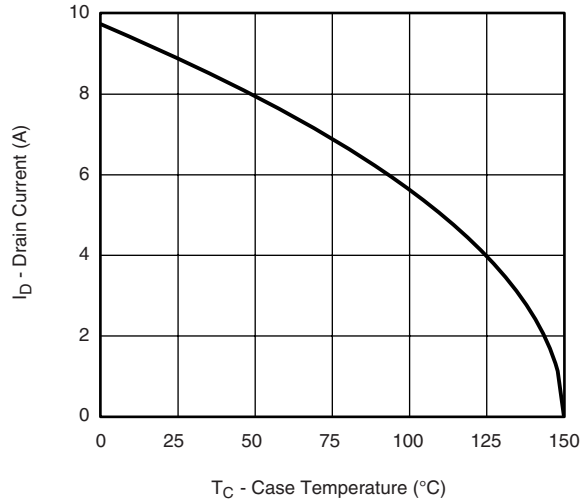


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

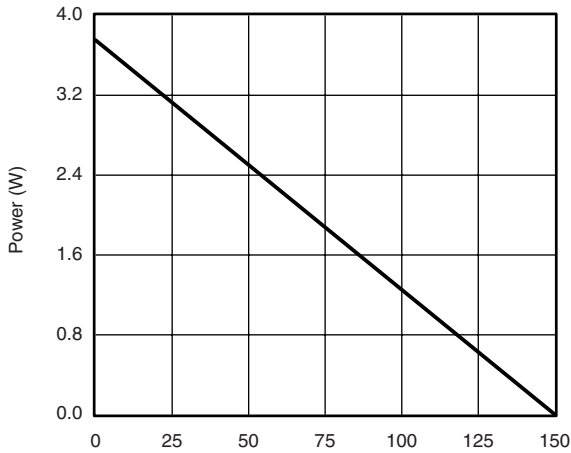




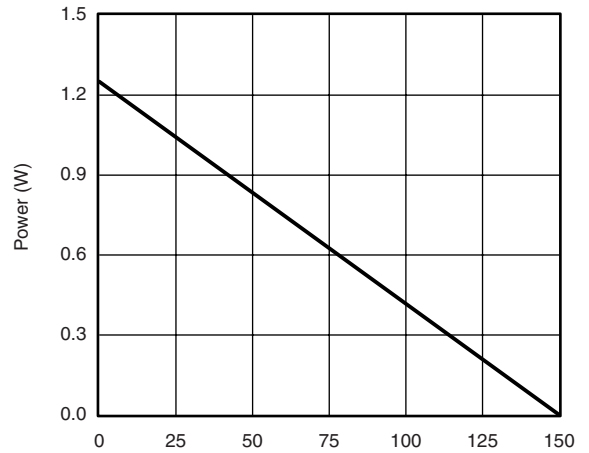
**MOSFET TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Current Derating\***



**Power, Junction-to-Foot**

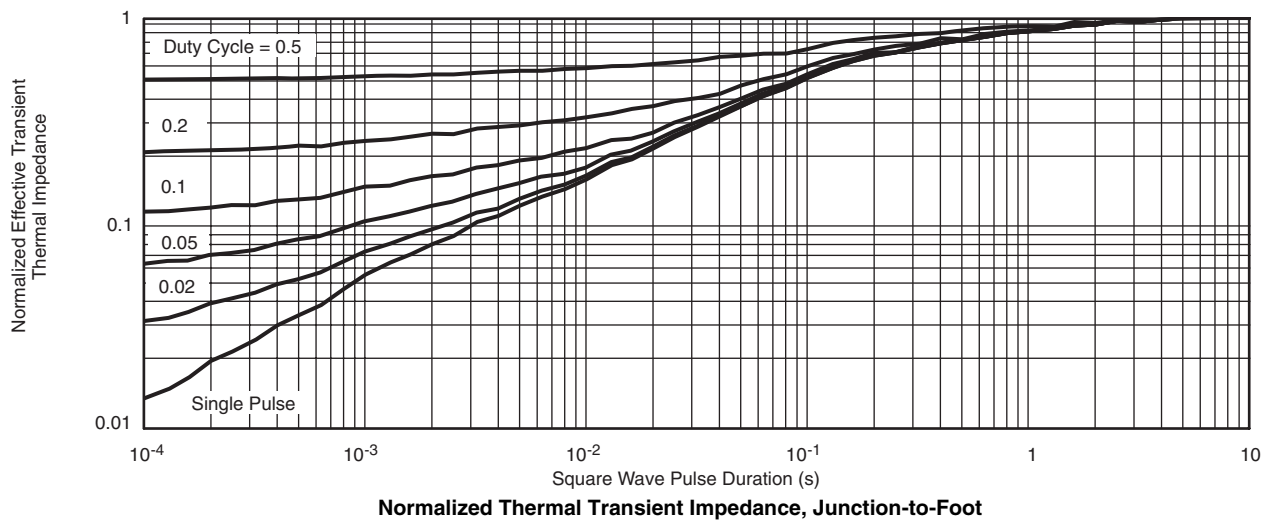
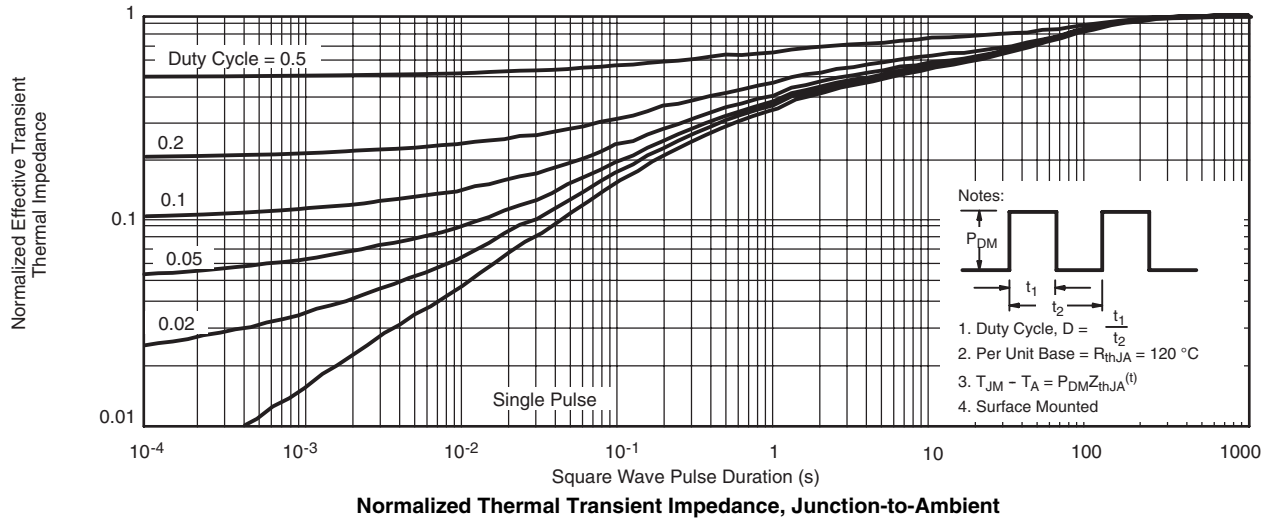


**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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